

THE UNITED STATES PATENT AND TRADEMARK OFFICE

**REVOCATION AND NEW POWER OF ATTORNEY AND
CHANGE OF CORRESPONDENCE ADDRESS**

I, ***Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.***, the Assignee of the entire right, title, and interest in the ***U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A***, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the ***U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A:***

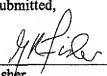
Customer Number: 76681

Please direct all correspondence in connection with said ***U.S. Patent Application(s) and/or Patent(s)*** to:

Customer Number: 76681

Respectfully submitted,

Date: 5/13/2008



Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

STATEMENT UNDER 37 CFR 3.73(b)


MEMC Electronic Materials, Inc., a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in *U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A*.

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to **MEMC Electronic Materials, Inc.** via Assignment(s) recorded with the United States Patent and Trademark Office at the *Reel/Frame Numbers on the attached Schedule A*.

The undersigned, **Dr. Graham Fisher, Director of Intellectual Property**, has full authorization to act on behalf of Assignee **MEMC Electronic Materials, Inc.**

Respectfully submitted,

Date: 5/13/2008



Dr. Graham Fisher
Director of Intellectual Property
MEMC Electronic Materials, Inc.

APPENDIX A
Owned by MEMC Electronic Materials, Inc.

ATTORNEY REFERENCE	CONF. NO.	PUBLICATION NO. & DATE	SERIAL NO. FILING DATE	PATENT NO. ISSUE DATE	CURRENT OWNER/ ASSIGNEE	REEL AND FRAME NO.	TITLE
MEMC2654.1	6190	US-2005-008389-A1 7/4/2002	10/23,506 2/11/2002	6,743,289 6/11/2004	MEMC Electronic Materials, Inc.	Division of 09/416,938 recorded at 01/08/19/0977	THERMAL ANNEALING PROCESS FOR PRODUCING LOW DEFECT DENSITY SINGLE CRYSTAL SILICON
MEMC2651	5650	US-2002-0134302-A1 9/26/2002	06/17,538 9/23/2001	6,579,382 6/17/2003	MEMC Electronic Materials, Inc.	01/1897/0283	HEAT SHIELD ASSEMBLY FOR CRYSTAL PULLER
MEMC2653	9826	US-2002-0134302-A1 9/26/2002	06/17,538 9/23/2001	6,435,474 6/20/2002	MEMC Electronic Materials, Inc.	01/0938/0274	NON-CONTAMINATING GAS-TIGHT VALVE FOR SEMI-CONDUCTOR APPLICATIONS
MEMC2657	6382	US-2002-0007779-A1 12/4/2002	09/505,269 2/16/2000	6,479,386 11/12/2002	MEMC Electronic Materials, Inc.	01/0633/0103	PROCESS FOR RECUING SURFACE VARIATIONS FOR POLISHED WAFER
MEMC2614	6202	US-2002-0007779-A1 12/4/2002	09/475,320 12/20/1999	6,638,357 10/28/2003	MEMC Electronic Materials, Inc.	01/0592/0082	METHOD FOR REVEALING AGGLOMERATED INTRINSIC POINT DEFECTS IN SEMICONDUCTOR CRYSTALS
MEMC2632	5009		09/502,340 2/10/2000	6,776,840 8/17/2004	MEMC Electronic Materials, Inc.	01/0585/0457	METHOD OF CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A LOCKED SEED LIFT GROWTH PROCESS
MEMC2633	5999		09/489,481 11/12/2000	6,315,628 11/13/2001	MEMC Electronic Materials, Inc.	Continuation of 09/167,747 recorded at 03/06/12/0596	CONTINUOUS OXIDATION PROCESS FOR CRYSTAL PULLING APPARATUS
MEMC2640.1	9314	US-2001-0008421-A1 19/2/003	09/699,200 11/21/2001	6,495,892 11/26/2002	MEMC Electronic Materials, Inc.	01/2627/0404	PROCESS FOR MAKING WAFERS FOR ION IMPLANTATION MONITORING
MEMC2641	4842		09/586,690 5/6/2000	6,444,027 9/5/2002	MEMC Electronic Materials, Inc.	01/1003/0186	MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS
MEMC2641.4	9780	US-2004-0041769-A1 3/8/2003	10/229,415 6/28/2002	6,652,650 11/25/2003	MEMC Electronic Materials, Inc.	Continuation of 09/596,890 recorded at 01/10/03/0186	MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS
MEMC2642	6444		09/723,847 11/23/2000	6,515,742 2/1/2003	MEMC Electronic Materials, Inc.	01/1320/0946	DEFECT CLASSIFICATION USING SCATTERED LIGHT INTENSITIES
MEMC2643	4589	US-2001-0037761-A1 11/8/2001	09/752,222 12/29/2000	6,598,096 7/22/2003	MEMC Electronic Materials, Inc.	01/1662/0217	AN EPITAXIAL SILICON WAFER FREE FROM AUTODOPING AND BACKSIDE HALO AND A METHOD AND APPARATUS FOR THE PREPARATION THEREOF
MEMC2644	4222		09/630,958 3/9/2000	6,484,855 6/20/2002	MEMC Electronic Materials, Inc.	01/1214/0312	METHOD AND APPARATUS FOR A WAFER CARRIER HAVING AN INSERT
MEMC2651	6610		09/603,666 2/14/2000	6,344,083 2/15/2002	MEMC Electronic Materials, Inc.	01/0763/0983	PROCESS FOR PRODUCING A SILICON MELT
MEMC2641.4	2620	US-2002-0020398-A1 2/21/2002	09/646,600 6/6/2001	6,662,645 11/25/2003	MEMC Electronic Materials, Inc.	Continuation of 09/509,586 recorded at 01/10/03/0083	PROCESS FOR PREPARING A SILICON MELT
MEMC2641.5	5192	US-2002-003887-A1 7/4/2002	10/336,676 10/12/2001	6,749,683 10/13/2004	MEMC Electronic Materials, Inc.	01/7220/0302	PROCESS FOR PRODUCING A SILICON MELT
MEMC2639	1032		09/621,525 3/6/2000	6,350,312 2/29/2002	MEMC Electronic Materials, Inc.	01/0684/0146 and 01/2139/0404	STRONTIUM DOPING OF MOLTEN SILICON FOR USE IN CRYSTAL GROWING PROCESS